Figure 1

S. Publication	PECVD Reaction	'Delta-n' Control Method	Post-dep. Thermal
Valence 1007	¥11		Treatment To (OC)
Valette S.,1987	Unknown	P doping	Not specified
Valette S.,1988	Unknown	P doping	400°C
Grand G., 1990	Unknown	P doping	1000°C
Liu K., 1995	Unknown	Content in Si, P	Not specified
Ojha S., 1998	Unknown	Ge, B, or P doping	Not specified
Canning J., 1998	Unknown	Ge doping	Not specified
Bulla D., 1998	TEOS	TEOS	Not specified
Johnson C., 1998	SiH ₄ + O ₂	Si ion Implantation	400°C
Boswell R. W., 1997	SiH ₄ + O ₂	SiH ₄ /O ₂ flow ratio	1000°C
Bazylenko M. V., 1995	$SiH_4 + O_2 + CF_4$	(SiH ₄ +O ₂)/CF ₄ flow ratio	Not specified
Bazylenko M. V., 1996	$SiH_4 + O_2 + CF_4$	(SiH ₄ +O ₂)/CF ₄ flow ratio	1000°C
Durandet A., 1996	$SiH_4 + O_2 + CF_4$	SiH ₄ /O ₂ /CF ₄ flow ratio	100°C
Kapser K., 1991	SiH ₄ + N ₂ O	SiH ₄ /N ₂ O flow ratio	1060°C
Lai Q., 1992	$SiH_4 + N_2O$	SiH ₄ /N ₂ O flow ratio	1100°C
Lai Q.,1993	$SiH_4 + N_2O$	SiH ₄ /N ₂ O flow ratio	1100°C
Pereyra I., 1997	SiH ₄ + N ₂ O	SiH ₂ /N ₂ O flow ratio	400°C
Alayo M., 1998	SiH ₄ + N ₂ O	SiH ₄ /N ₂ O flow ratio	1000°C
Kenyon T., 1997	$SiH_4 + N_2O + Ar$	SiH ₄ /N ₂ O/Ar flow ratio	1000°C
Lam D. K. W., 1984	$SiH_4 + N_2O + NH_3$	SiH ₄ /N ₂ O/NH ₃ flow ratio	Not specified
Bruno F., 1991	$SiH_4 + N_2O + NH_3$	SiH ₄ /N ₂ O/NH ₃ flow ratio	1100°C
Yokohama S., 1995	$SiH_4 + N_2O + NH_3$	SiH ₄ /N ₂ O/NH ₃ flow ratio	Not specified
Agnihotri O. P., 1997	$SiH_4 + N_2O + NH_3$	SiH ₂ /N ₂ O/NH ₃ flow ratio	700-900°C
Germann R., 1999	$SiH_4 + N_2O + NH_3$	Unknown	1100°C
Offrein B., 1999	$SiH_4 + N_2O + NH_3$	Unknown	1150°C
Hoffmann M., 1995	$SiH_4 + N_2O + NH_3 + Ar$	SiH ₄ /N ₂ O/NH ₄ /Ar flow ratio	Not specified
Hoffmann M., 1997	$SiH_4 + N_2O + NH_3 + Ar$	SiH ₄ /N ₂ O/NH ₃ /Ar flow ratio	Not specified
Tu Y., 1995	$SiH_4 + N_2O + NH_3 + N_2$	N ₂ O/(N ₂ O + NH ₃) flow ratio	1050°C
Poenar D., 1997	$SiH_4 + N_2O + NH_3 + N_2$	SiH ₂ /N ₂ O/NH ₂ /N ₂ , flow ratio	850°C
Ridder R., 1998	$SiH_4 + N_2O + NH_3 + N_2$	SiH ₄ /N ₂ O/NH ₃ /Ar flow ratio	1100°C
Worhoff K., 1999	$SiH_4 + N_2O + NH_3 + N_2$	SiH ₄ /N ₂ O/NH ₃ /N ₂ flow ratio	1150°C
Bulat E.S., 1993	$SiH_4 + N_2O + N_2 + O_2 + He + CF_4$	SiH ₄ /(N ₂ O/N ₂)/O ₂ /CF ₄ flow ratio	425°C
This Patent Application	$SiH_4 + N_2O + PH_3 + N_2$	Patented Pending Method	650°C

Figure 2

		Ŧ	Ī	Ι	Ŧ	Ŧ	0	٨	i <u>s</u>	is:	Z	Ξ	Si	ίς.
		но-н	SIO-H	SiN-H	Si:N-H	SI-H	0≓!S	N=N	S-0-IS	Si-O-S	Si-ON	HO-is	Si-O-Si	Si-O-Si
					•				•	0,			0)	0,
3.0	Min	3550	3470	3380	3300	2210	1800	1530	1080	1000	910	860	740	410
FTIR 1st mode (cm-1)	Ave	3650	3510	3420	3380	2260	1875	1555	1180	1080	950	885	810	460
4 50	Max	3750	3550	3460	3460	2310	1950	1580	1280	1160	990	910	880	510
1st mode (µm)	Min	2.817	2.882	2.959	3.030	4.525	5.556	6.536	9.259	10.000	10.989	11.628	13.514	24.390
	Ave	2.740	2.849	2.924	2.959	4.425	5.333	6.431	8.475	9.259	10.526	11.299	12.346	21.739
	Max	2.667	2.817	2.890	2.890	4.329	5.128	6.329	7.813	8.621	10.101	10.989	11.364	19.608
2nd mode (µm)	Min	1.408	1.441	1.479	1.515	2.262	2.778	3.268	4.630	5.000	5.495	5.814	6.757	12.195
	Ave	1.370	1.425	1.462	1.479	2.212	2.667	3.215	4.237	4.630	5.263	5.650	6.173	10.870
	Max	1.333	1.408	1.445	1.445	2.165	2.564	3.165	3.906	4.310	5.051	5.495	5.682	9.804
0	Min	0.939	0.961	0.986	1.010	1.508	1.852	2.179	3.086	3.333	3.663	3.876	4.505	8.130
3rd mode (µm)	Ave	0.913	0.950	0.975	0.986	1.475	1.778	2.144	2.825	3.086	3.509	3.766	4.115	7.246
	Max	0.889	0.939	0.963	0.963	1.443	1.709	2.110	2.604	2.874	3.367	3.663	3.788	6.536
0 %	Min	0.704	0.720	0.740	0.758	1.131	1.389	1.634	2.315	2.500	2.747	2.907	3.378	6.098
4th mode (µm)	Ave	0.685	0.712	0.731	0.740	1.106	1.333	1.608	2.119	2.315	2.632	2.825	3.086	5.435
	Max	0.667	0.704	0.723	0.723	1.082	1.282	1.582	1.953	2.155	2.525	2.747	2.841	4.902
Sth mode (µm)	Min	0.563	0.576	0.592	0.606	0.905	1.111	1.307	1.852	2.000	2.198	2.326	2.703	4.878
	Ave	0.548	0.570	0.585	0.592	0.885	1.067	1.286	1.695	1.852	2.105	2.260	2.469	4.348
	Max	0.533	0.563	0.578	0.578	0.866	1.026	1.266	1.563	1.724	2.020	2.198	2.273	3.922
eth mode (µm)	Min	0.469	0.480	0.493	0.505	0.754	0.926	1.089	1.543	1.667	1.832	1.938	2.252	4.065
	Ave	0.457	0.475	0.487	0.493	0.737	0.889	1.072	1.412	1.543	1.754	1.883	2.058	3.623
	Max	0.444	0.469	0.482	0.482	0.722	0.855	1.055	1.302	1.437	1.684	1.832	1.894	3.268
7th mode (µm)	Min	0.402	0.412	0.423	0.433	0.646	0.794	0.934	1.323	1.429	1.570	1.661	1.931	3.484
	Ave	0.391	0.407	0.418	0.423	0.632	0.762	0.919	1.211	1.323	1.504	1.614	1.764	3.106
	Max	0.381	0.402	0.413	0.413	0.618	0.733	0.904	1.116	1.232	1.443	1.570	1.623	2.801
8th mode (µm)	Min	0.352	0.360	0.370	0.379	0.566	0.694	0.817	1.157	1.250	1.374	1.453	1.689	3.049
	Ave	0.342	0.356	0.365	0.370	0.553	0.667	0.804	1.059	1.157	1.316	1.412	1.543	2.717
	Max	0.333	0.352	0.361	0.361	0.541	0.641	0.791	0.977	1.078	1.263	1.374	1.420	2.451

Figure 3a

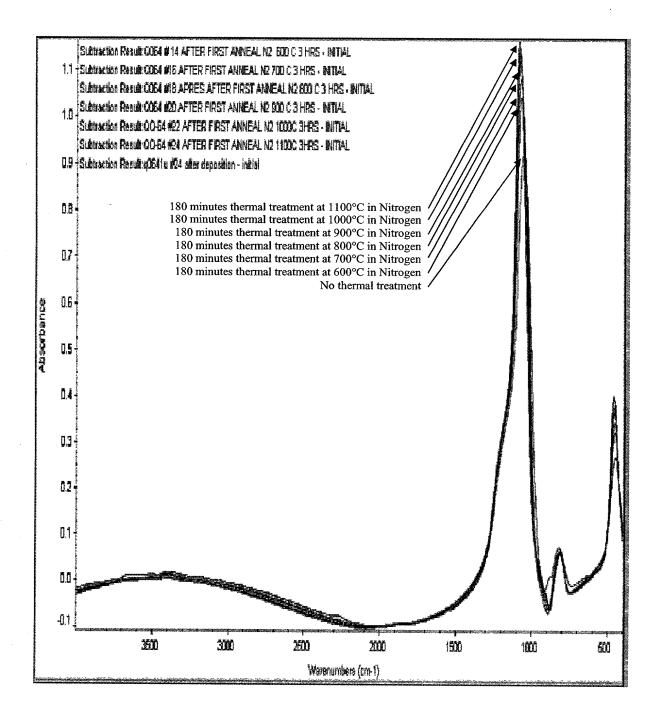


Figure 3b

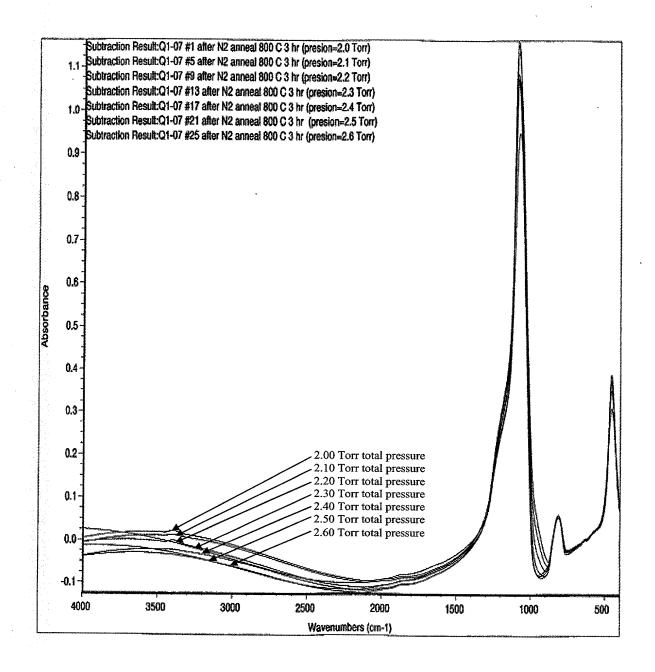


Figure 3c

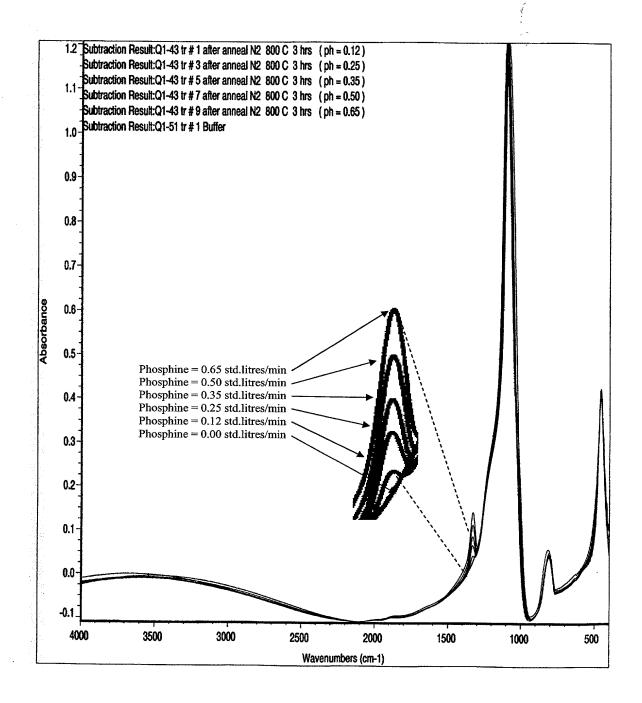


Figure 3d

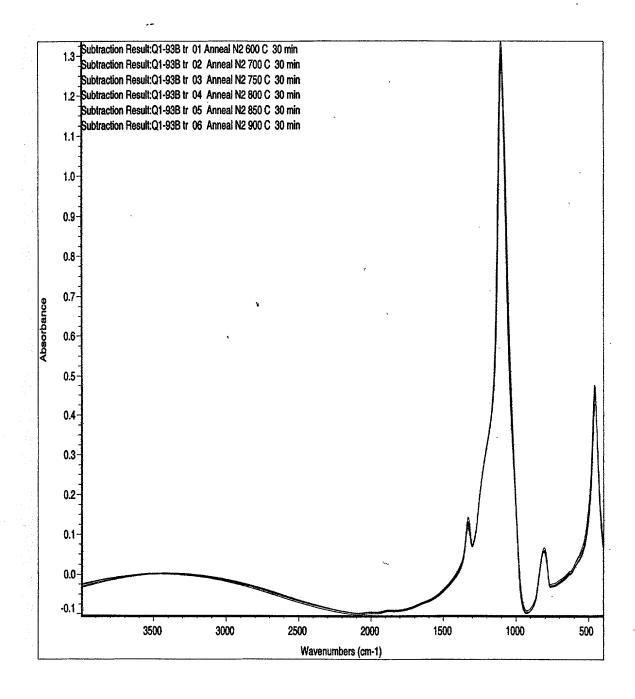


Figure 4a

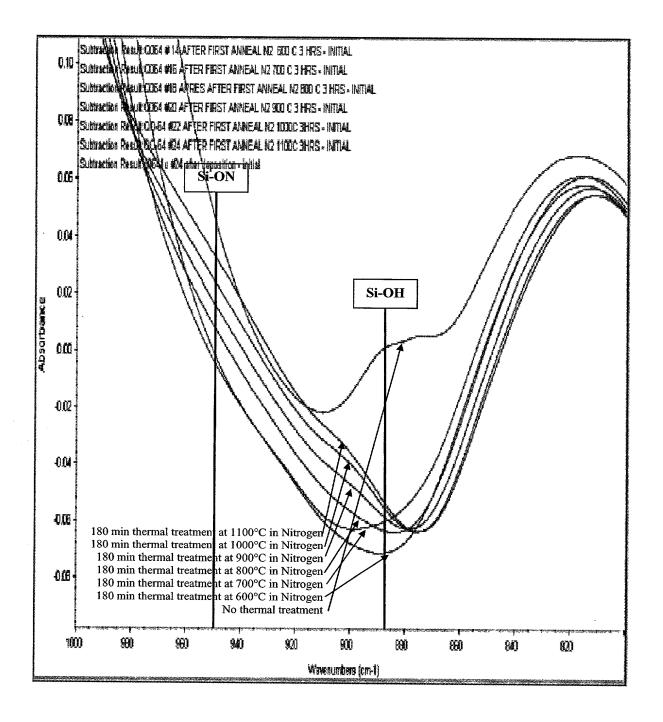


Figure 4b

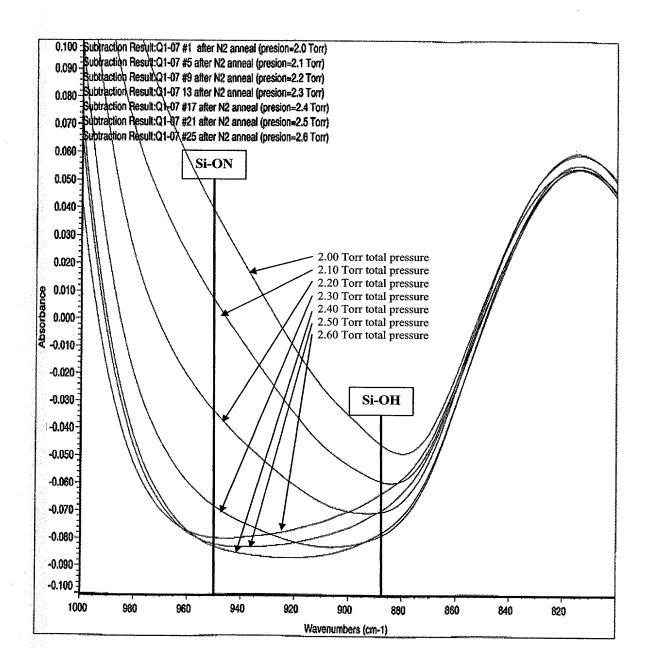


Figure 4c

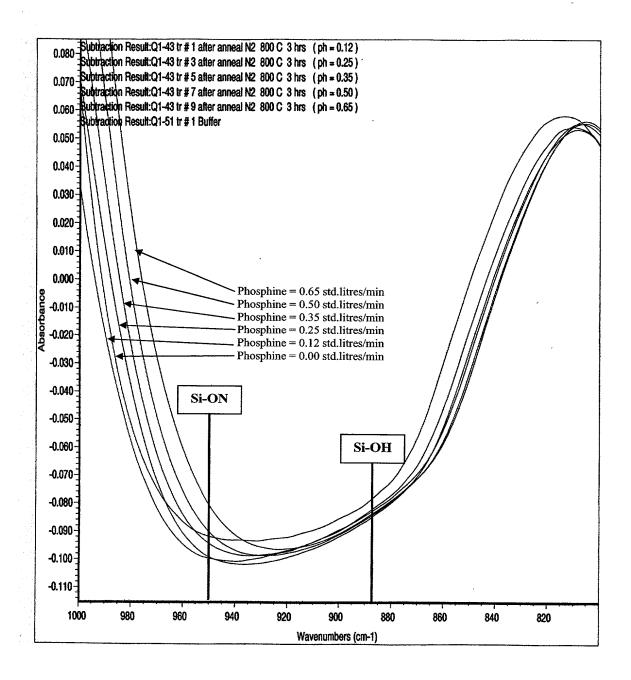


Figure 4d

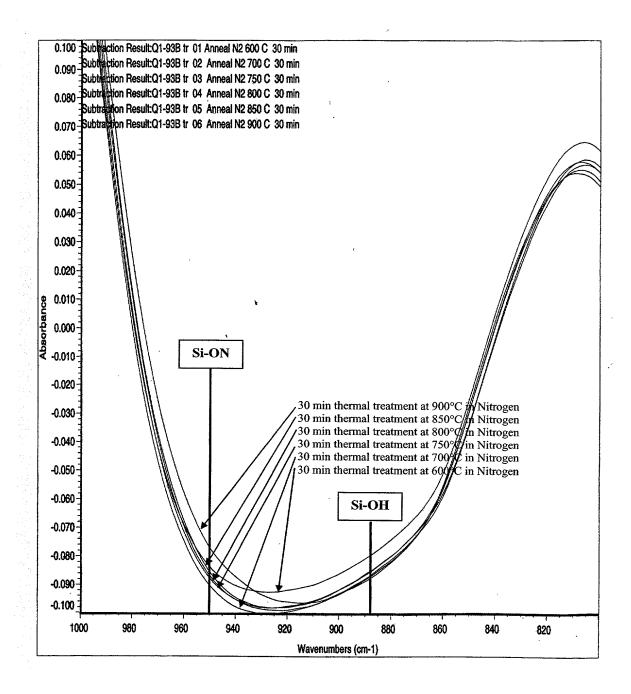


Figure 5c

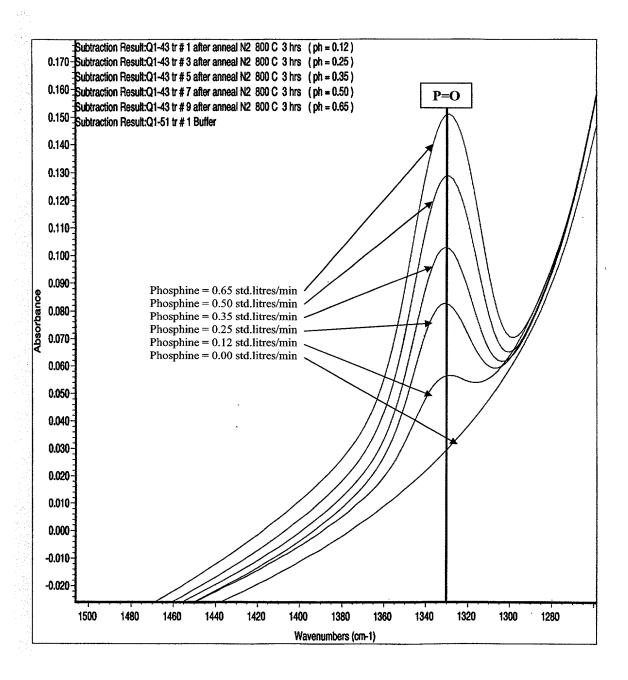


Figure 5d

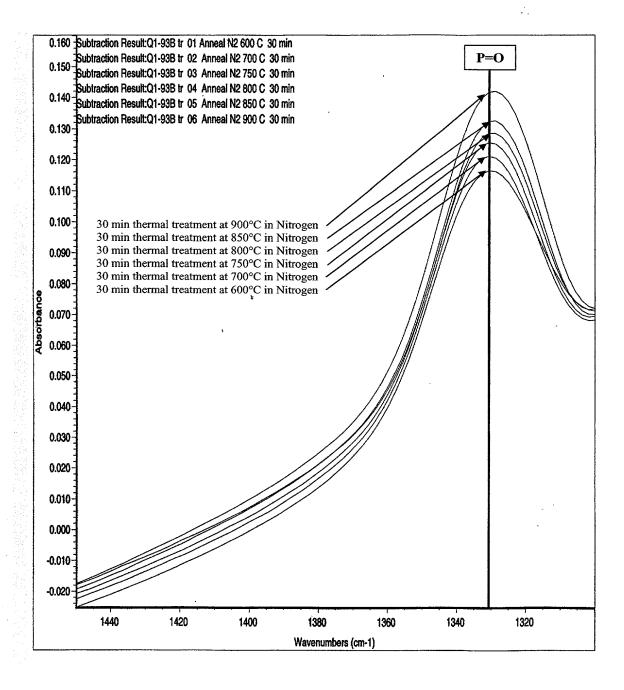


Figure 6a

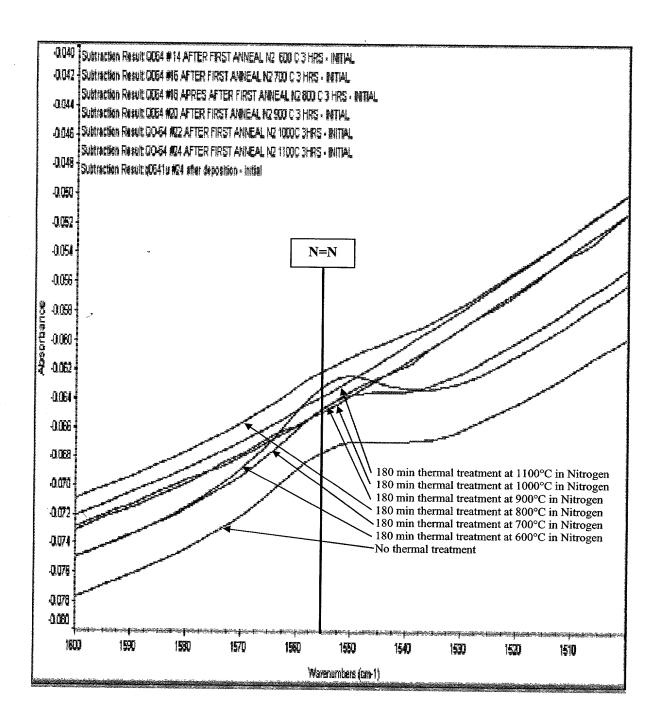


Figure 6b

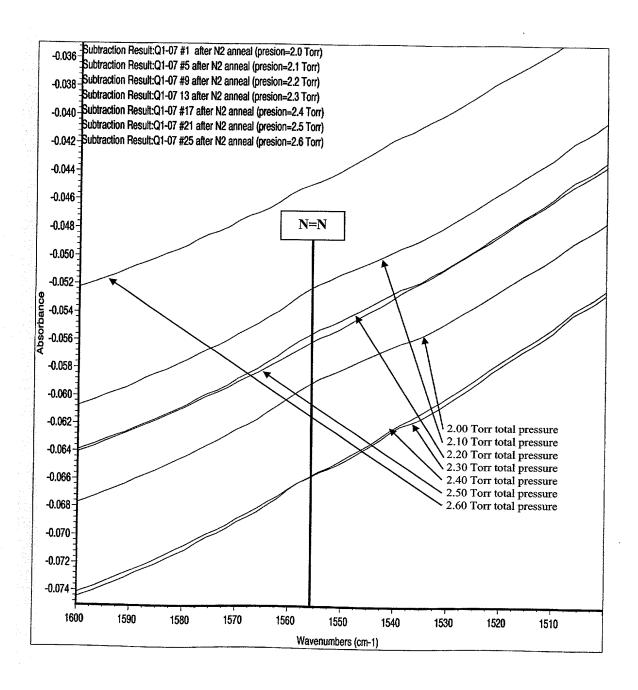


Figure 6c

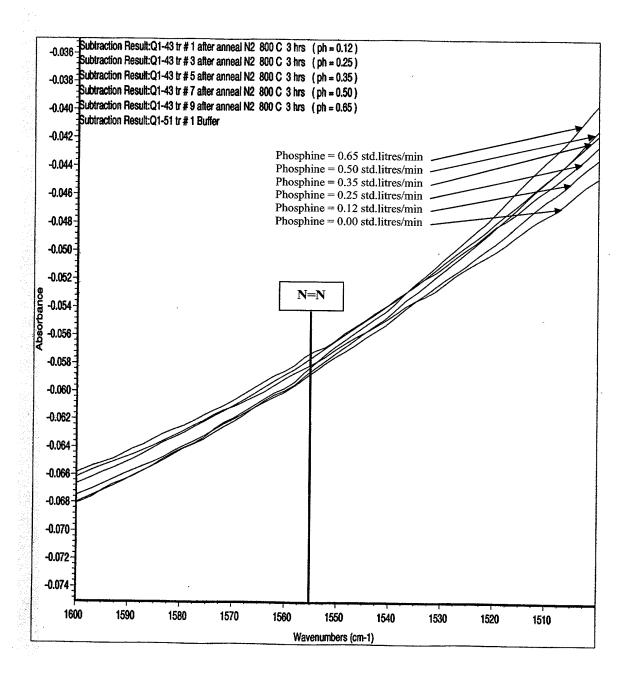


Figure 6d

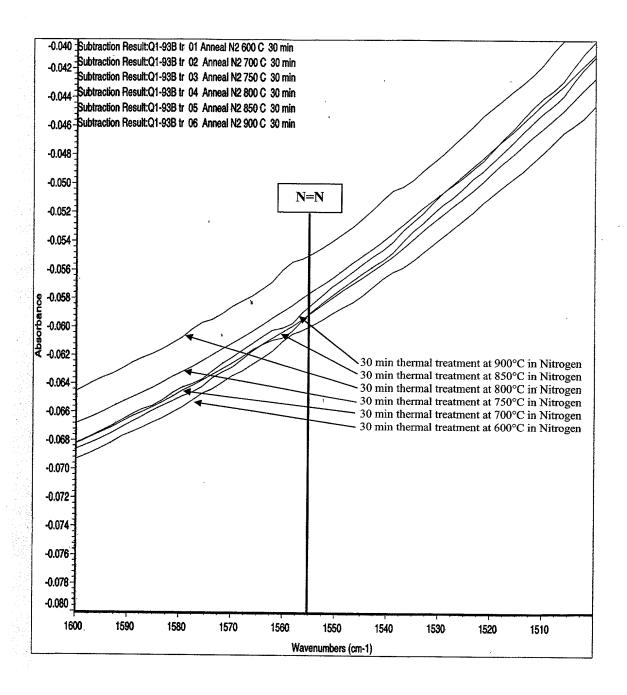


Figure 7a

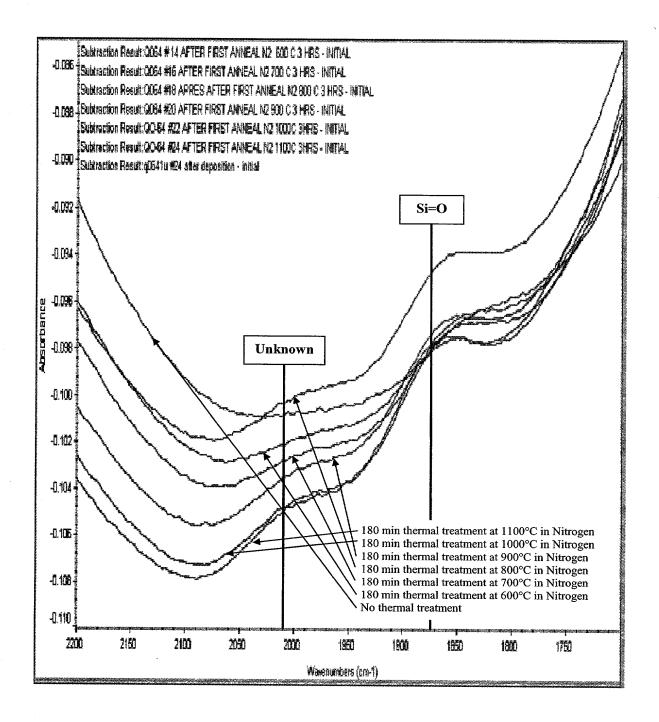


Figure 7b

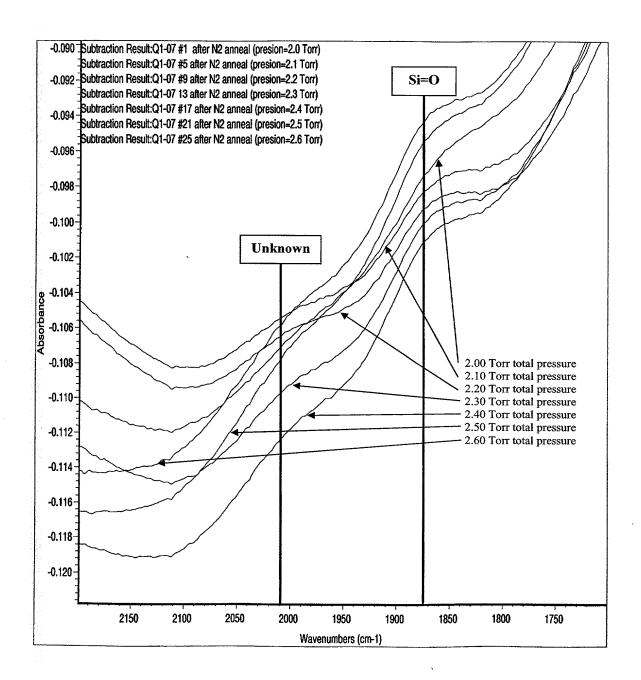


Figure 7c

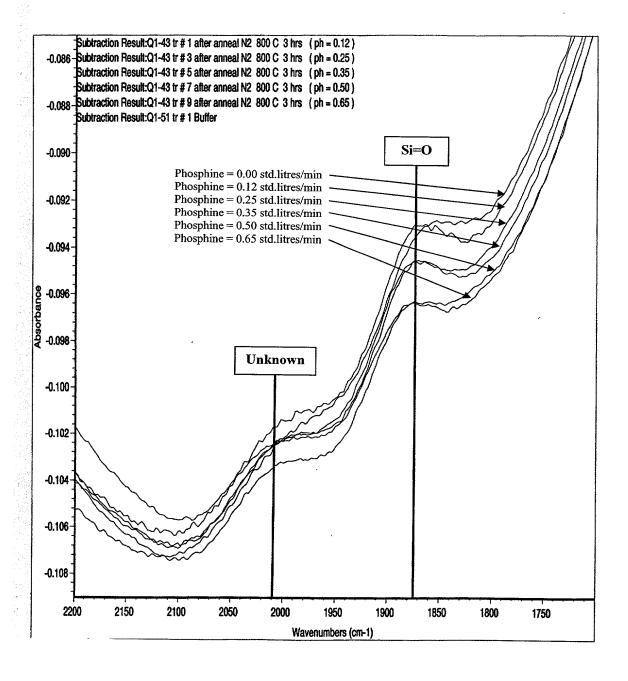


Figure 7d

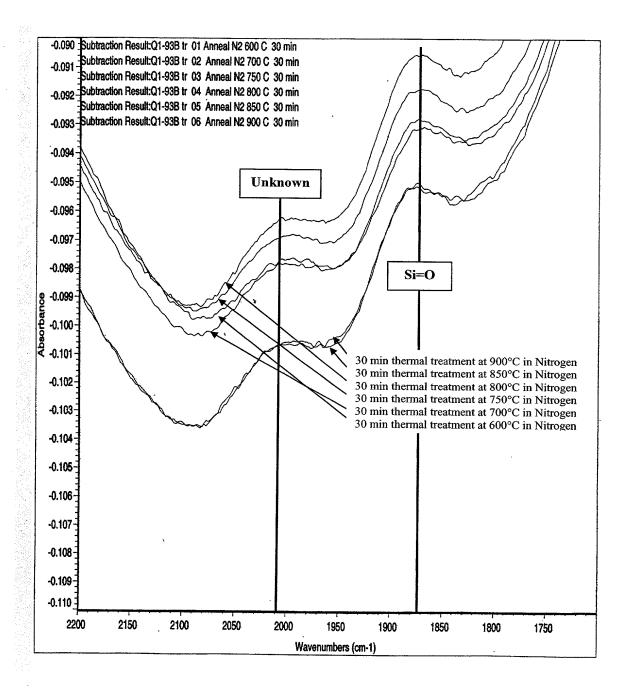


Figure 8a

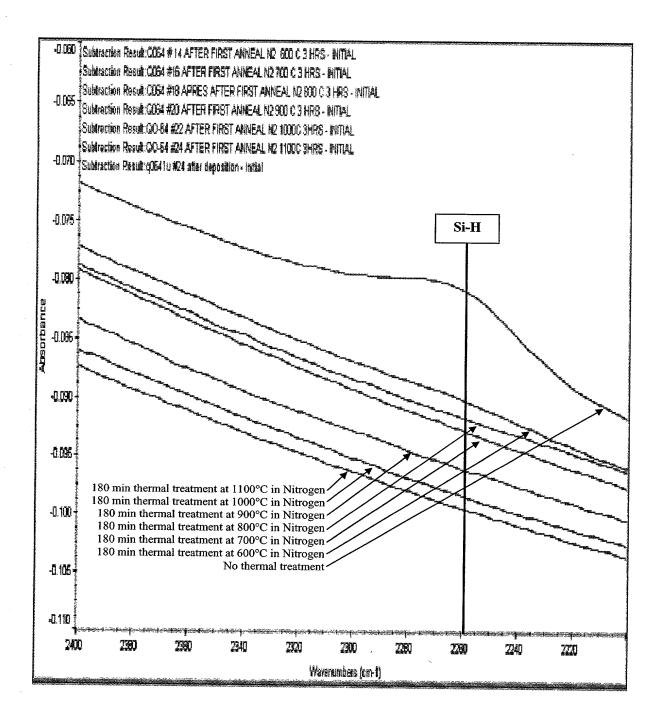


Figure 8b

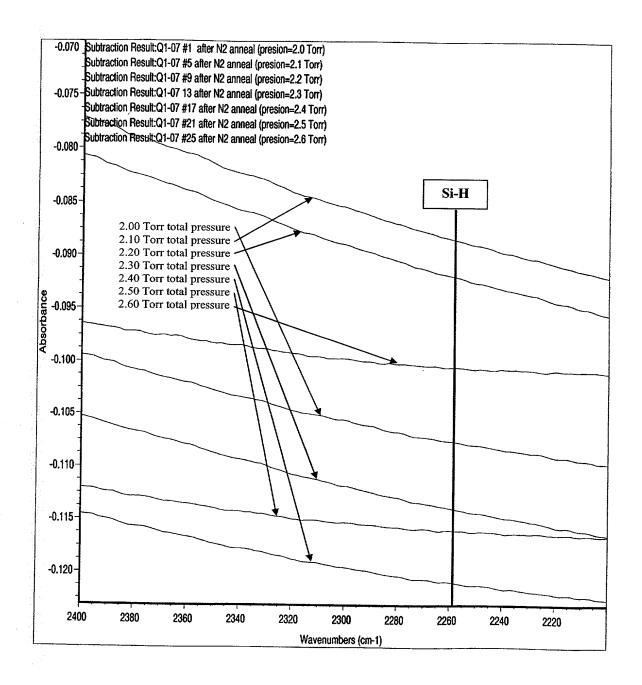


Figure 8c

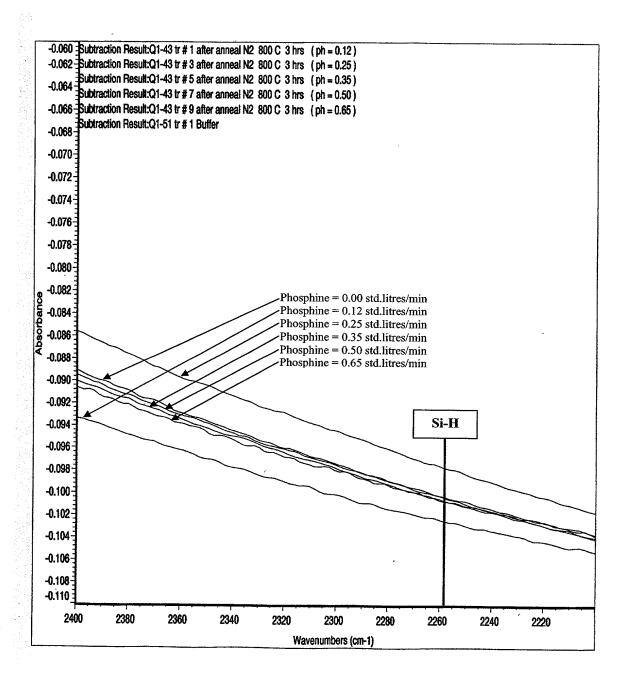


Figure 8d

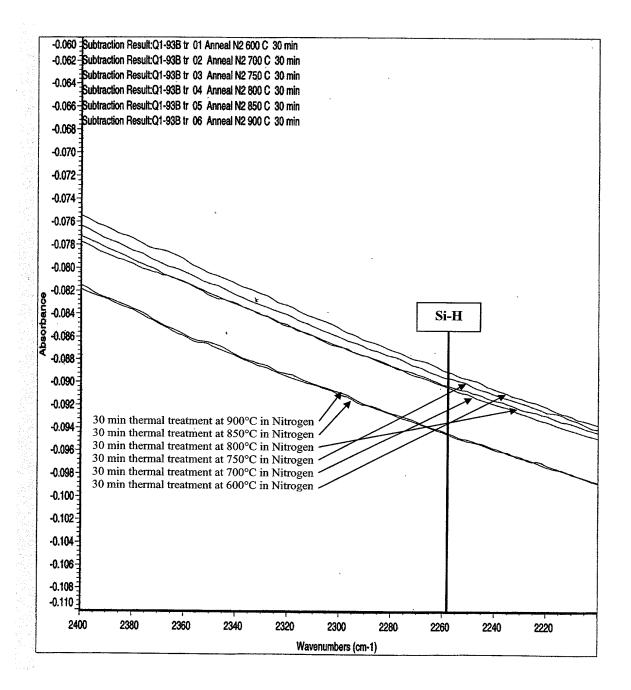


Figure 9a

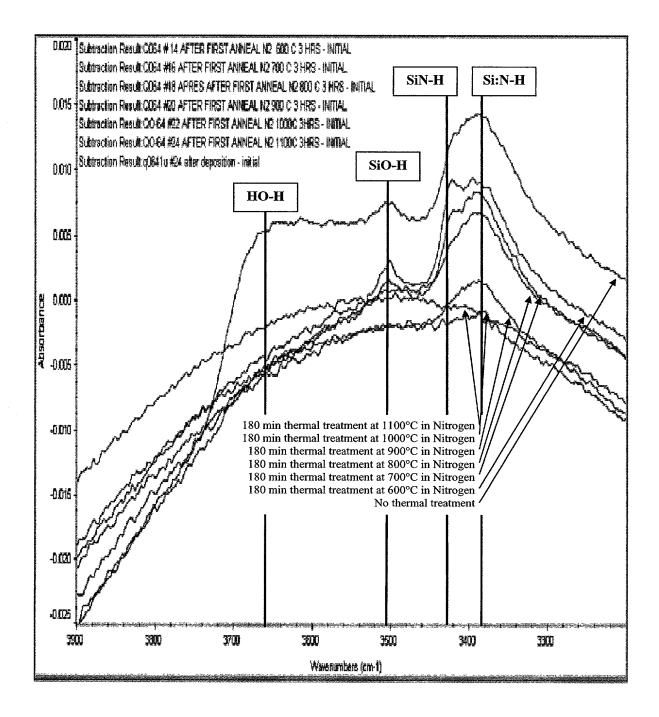


Figure 9b

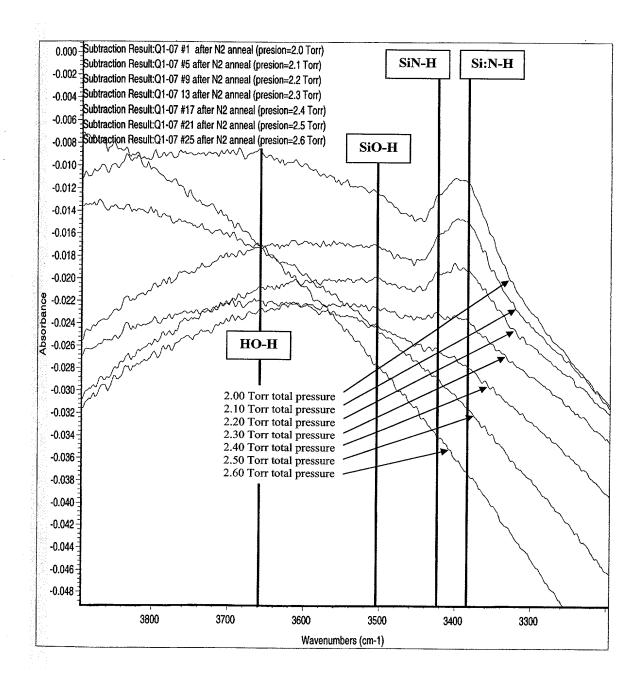


Figure 9c

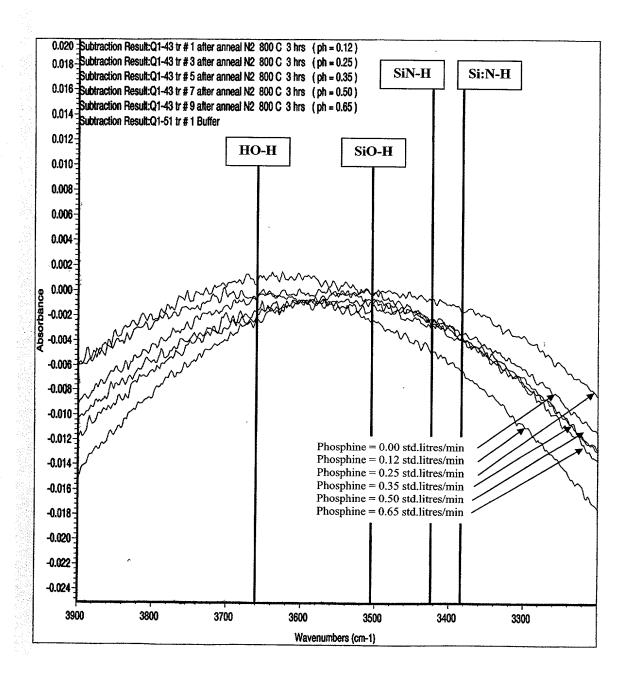


Figure 9d

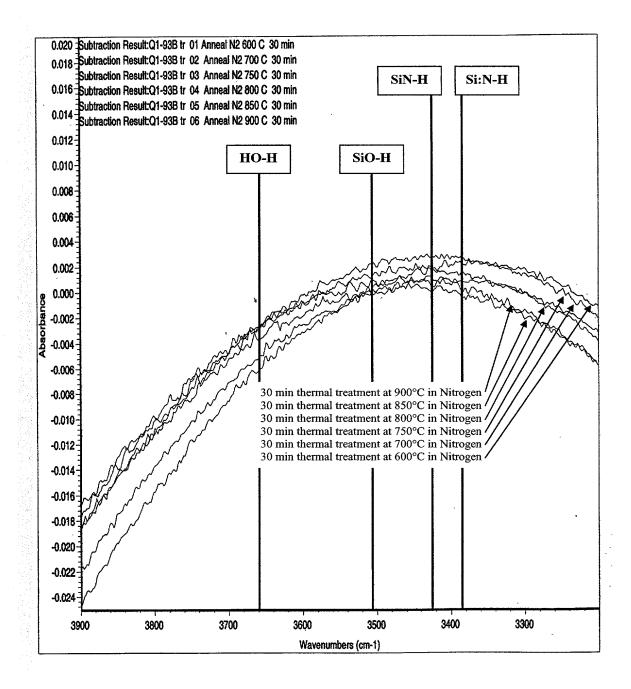
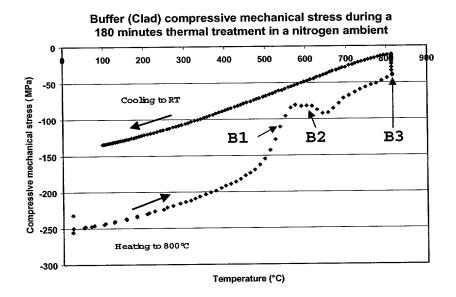


Figure 10



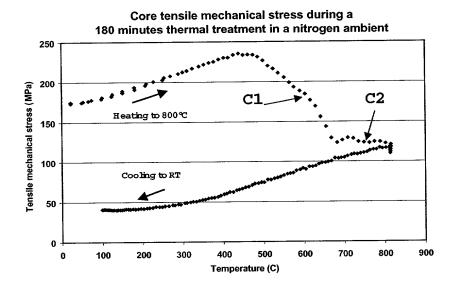
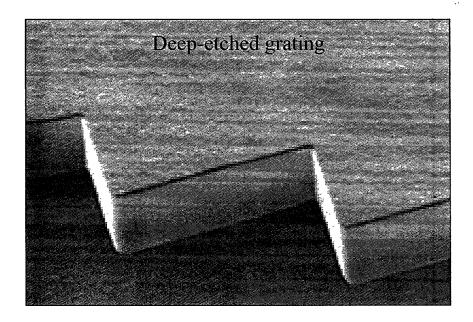


Figure 11



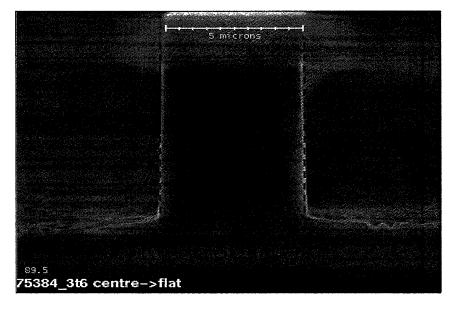


Figure 12

Tensile stress Core

(Core wants to contract)

Desired vertical deep-etched profile

Compressive stress Buffer (Clad)
(Buffer (Clad) wants to expand)

Tensile stress Core

(Core wants to contract)

Desired vertical deep etched profile

Compressive stress Buffer (Clad)

(Buffer (Clad) wants to expand).

Tensile stress Core

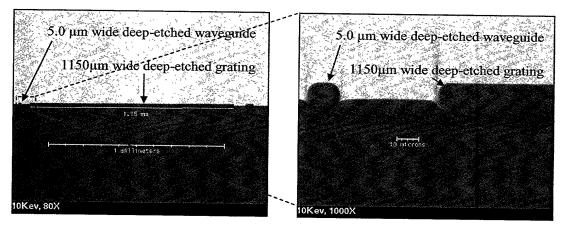
(Core wants to contract)

Desired vertical deep-etched profile

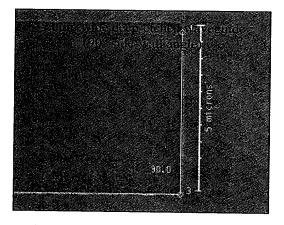
Compressive stress Buffer (Clad)

(Buffer (Clad) wants to expand)

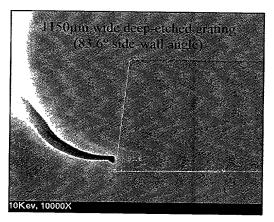
Figure 13



The relative position between an isolated $5.0\mu m$ wide deep-etched waveguide and its neighboring $1150\mu m$ wide deep-etched grating at two different magnifications.

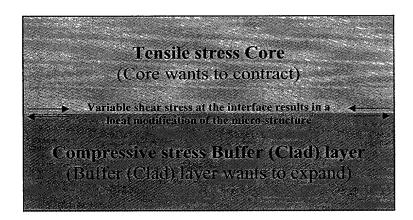


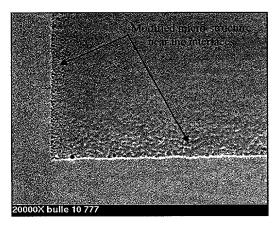
The side-wall of the 5.0µm wide deepetched waveguide facing the neighboring grating has a slope of about 90°.



The side-wall of the 1150µm wide deepetched grating facing the neighboring deep-etched waveguide has a much smaller slope of about 84°.

Figure 14





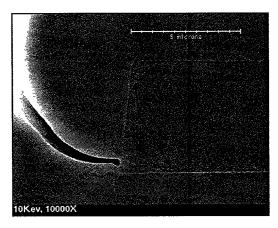
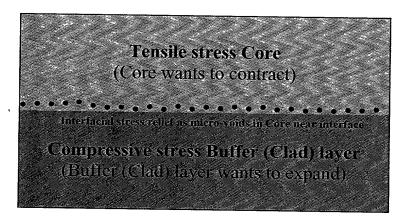
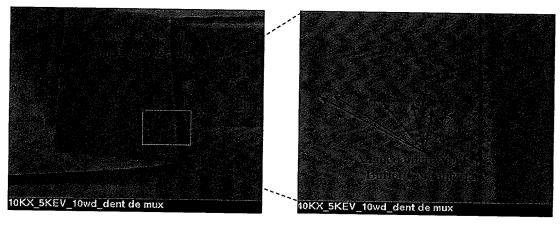


Figure 15





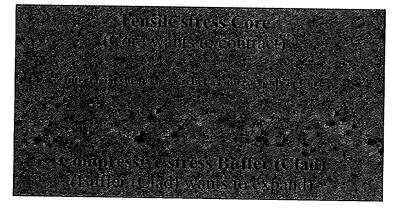
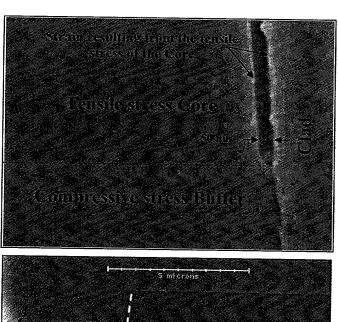
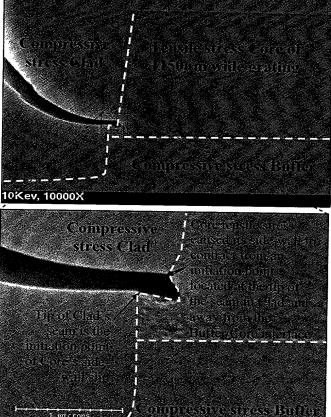


Figure 16

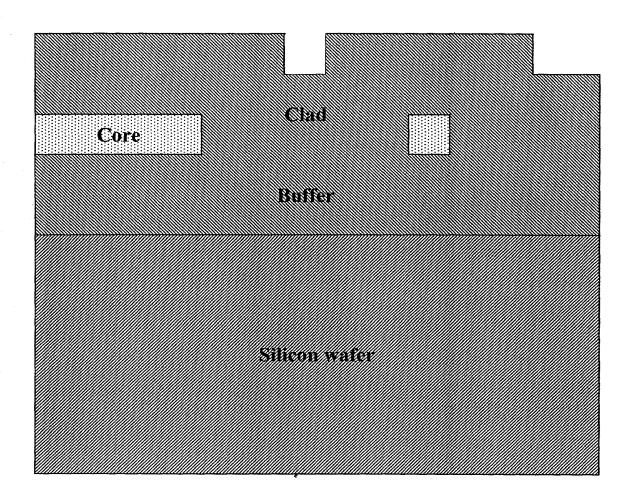




1 microns

10kev 37000x

Figure 17



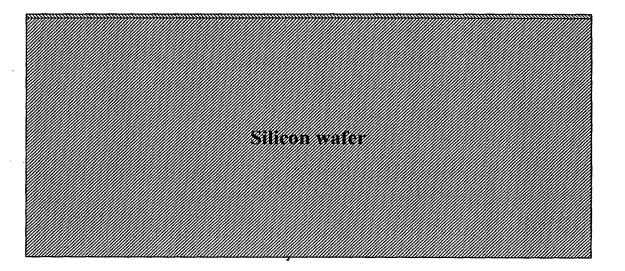


Figure 18b

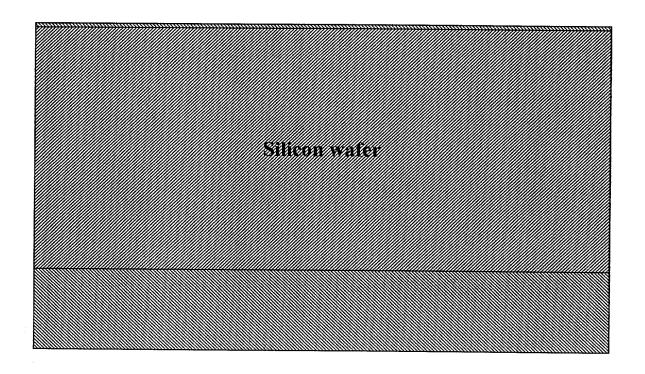


Figure 18c

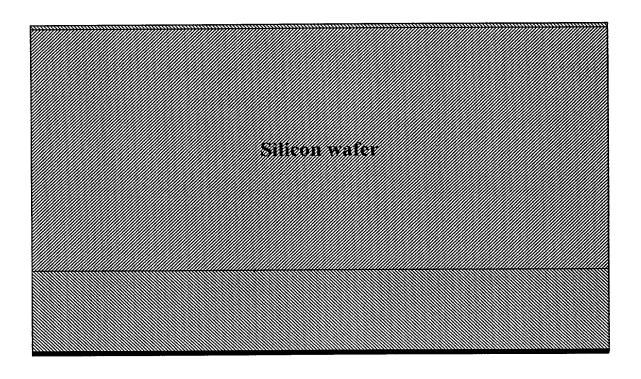


Figure 18d

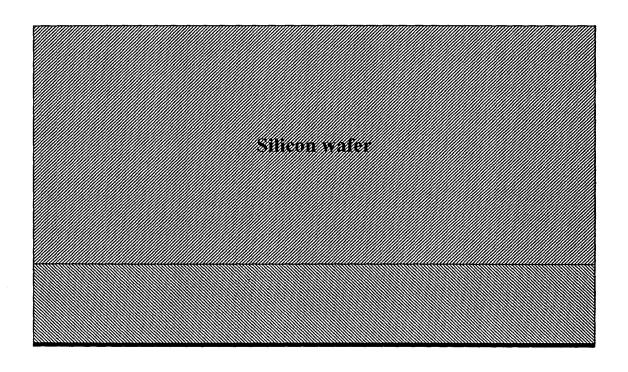


Figure 18e

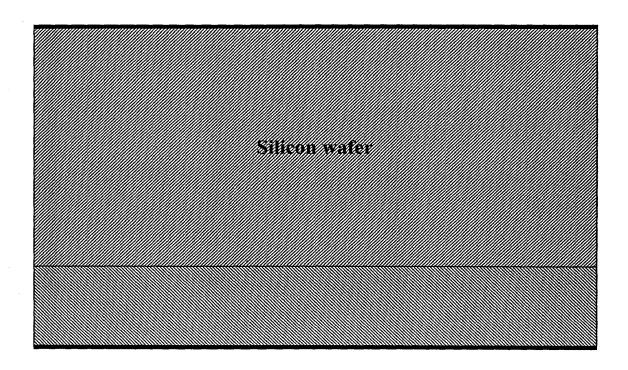


Figure 18f

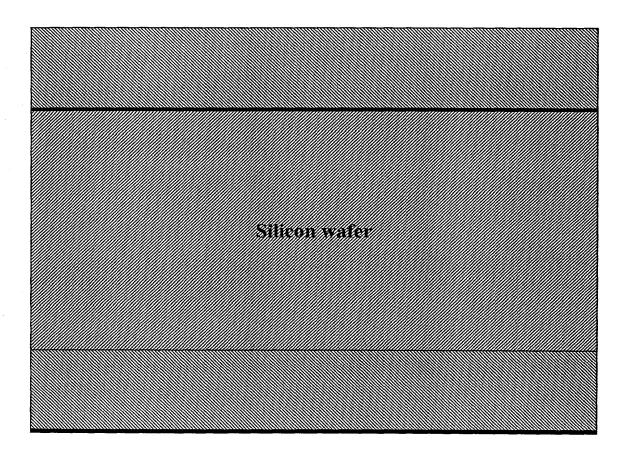


Figure 18g

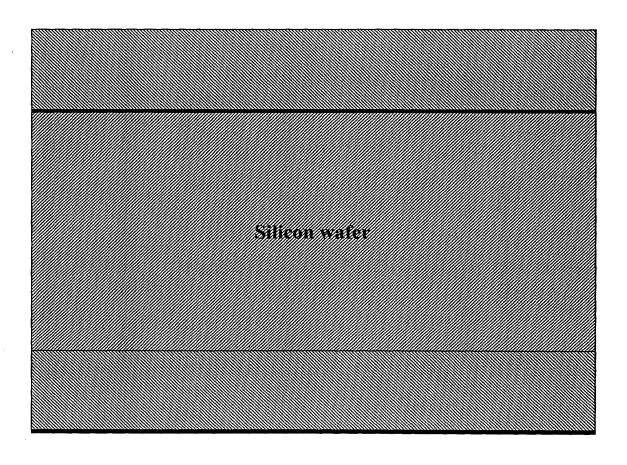


Figure 18h

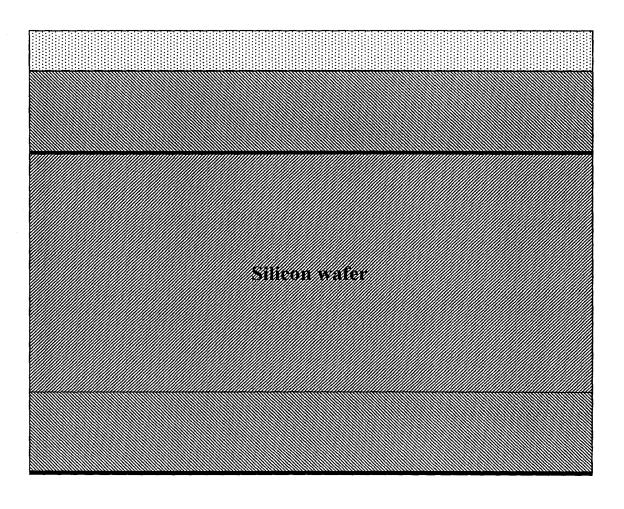
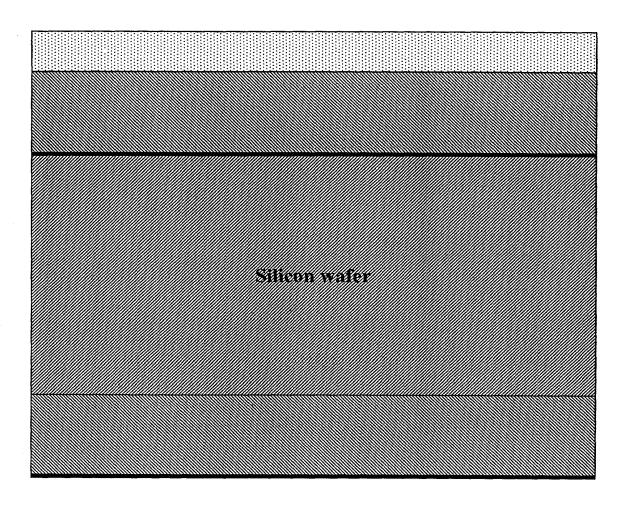


Figure 18i



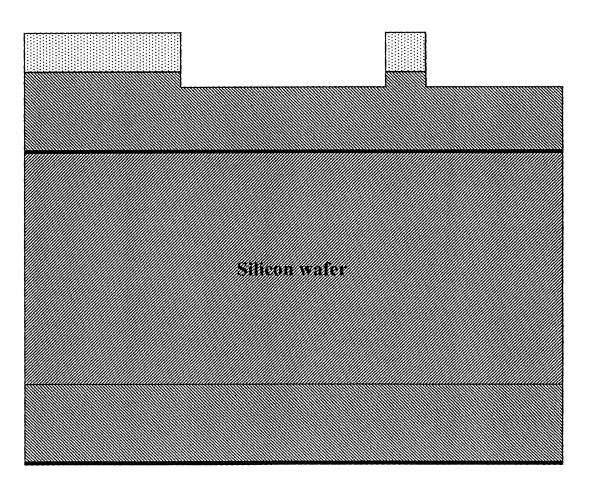


Figure 18k

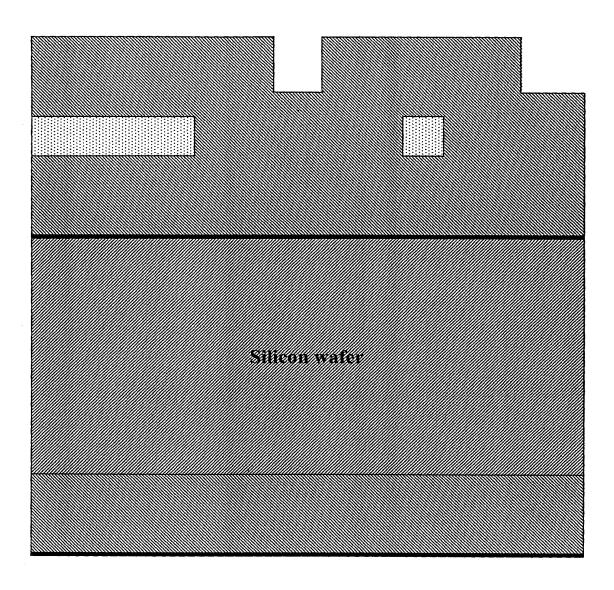


Figure 181

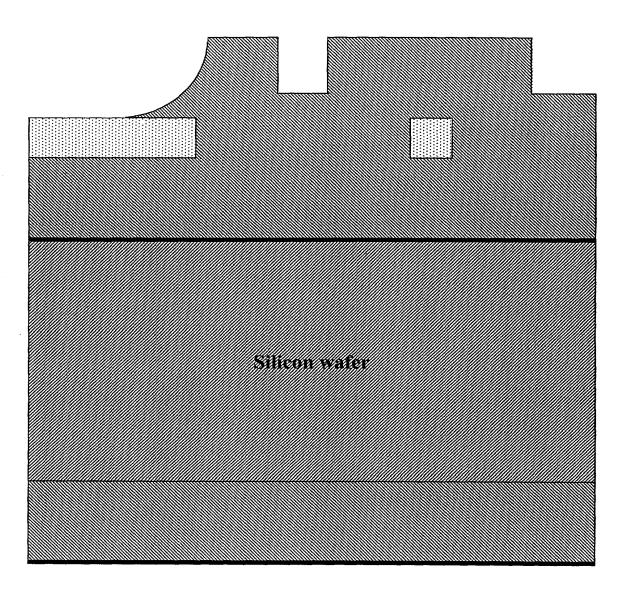


Figure 19

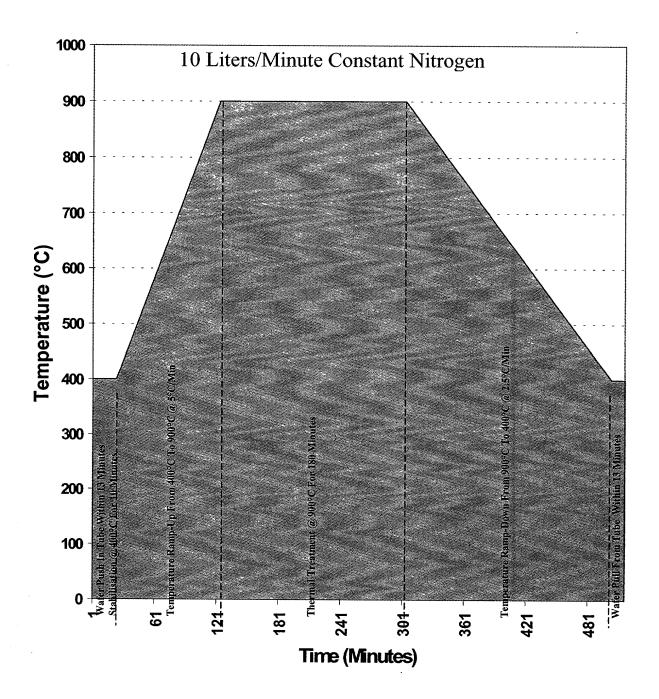


Figure 20

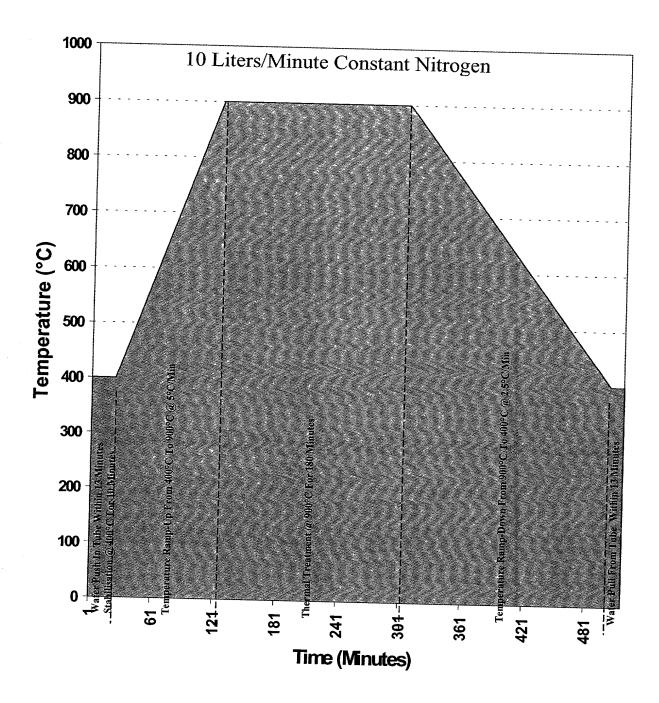


Figure 21

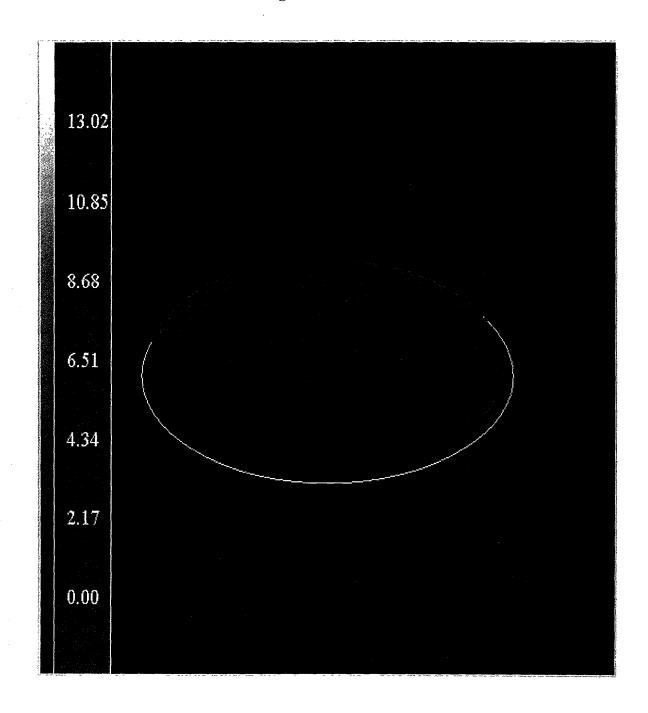


Figure 22

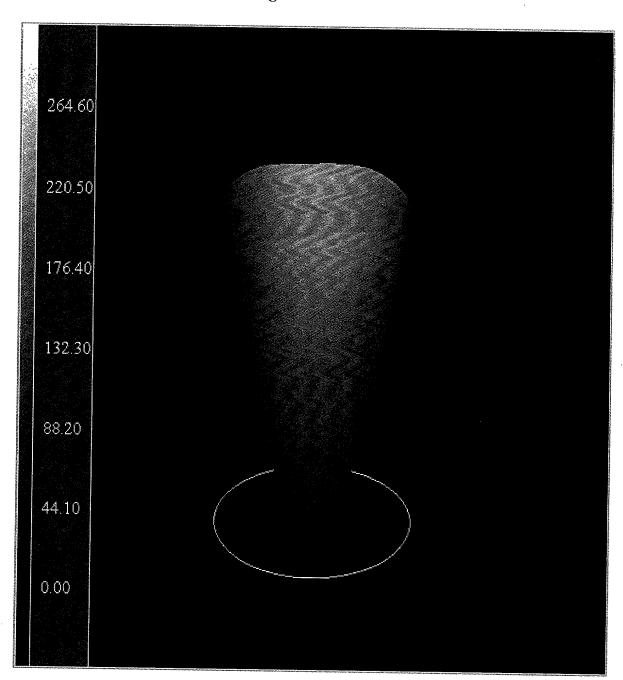


Figure 23

